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Silicon Switching Diode BAS16WT1G

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Symbol	Rating	Value	Unit
V _R	Continuous Reverse Voltage	100	V
I _R	Recurrent Peak Forward Current	200	mA
I _{FM(surge)}	Peak Forward Surge Current Pulse Width = 10 μs	500	mA
P _D	Total Power Dissipation, One Diode Loaded $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	200 1.6	mW mW/°C
T _J , T _{stg}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

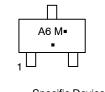
THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient One Diode Loaded Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	625	°C/W





MARKING DIAGRAM



A6 = Specific Device Code M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS16WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel
SBAS16WT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel

DISCONTINUED (Note 1)

NSVBAS16WT3G	SC-70	10,000 / Tape &	
	(Pb-Free)	Reel	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on <u>www.onsemi.com</u>.

BAS16WT1G

Symbol	Characteristic	Min	Max	Unit
V _F	Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$	- - - -	715 866 1000 1250	mV
I _R	Reverse Current $(V_R = 100 V)$ $(V_R = 75 V, T_J = 150^{\circ}C)$ $(V_R = 25 V, T_J = 150^{\circ}C)$	- - -	1.0 50 30	μΑ
CD	Capacitance (V _R = 0, f = 1.0 MHz)	-	2.0	pF
t _{rr}	Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}, R_L = 50 \Omega$) (Figure 1)	-	6.0	ns
QS	Stored Charge (I _F = 10 mA to V _R = 6.0 V, R _L = 500 Ω) (Figure 2)	-	45	PC
V_{FR}	Forward Recovery Voltage $(I_F = 10 \text{ mA}, t_r = 20 \text{ ns})$ (Figure 3)	-	1.75	V

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

BAS16WT1G

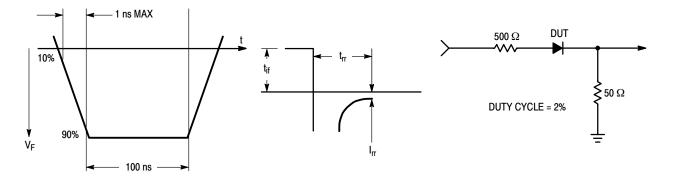


Figure 1. Reverse Recovery Time Equivalent Test Circuit

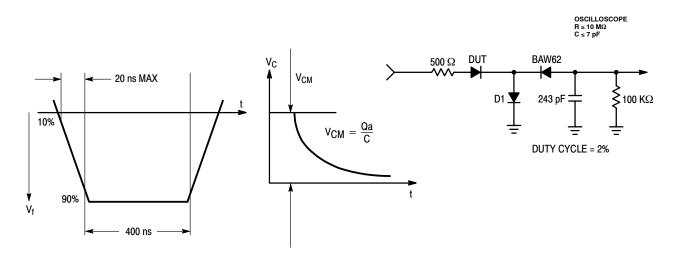


Figure 2. Stored Charge Equivalent Test Circuit

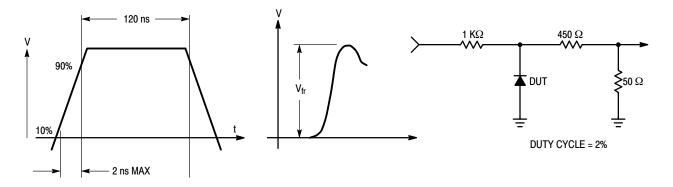


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

BAS16WT1G

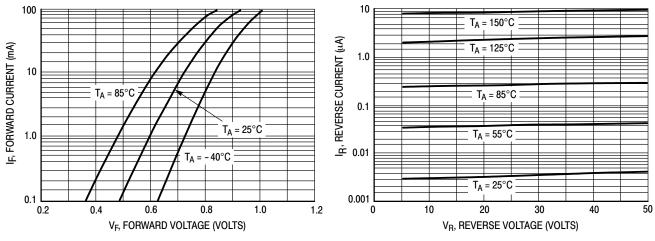
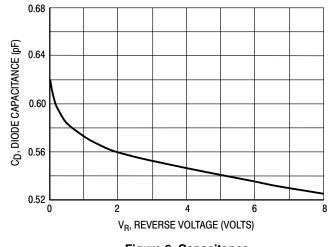


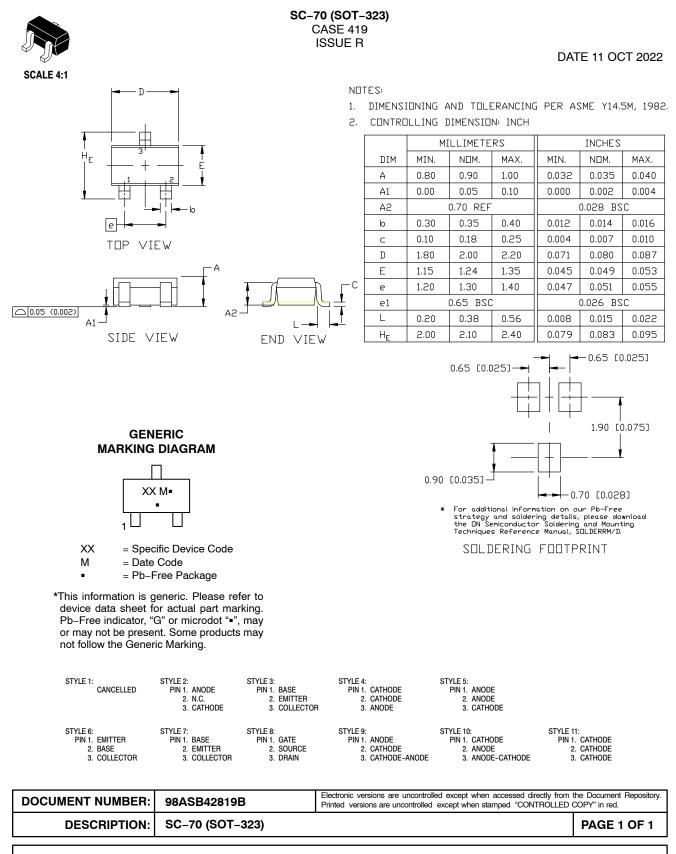


Figure 5. Leakage Current





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